

DATA SHEET

PDTA114E series
PNP resistor-equipped transistors;
 $R1 = 10 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$

Product specification
Supersedes data of 2003 Apr 10

2004 Aug 02

**PNP resistor-equipped transistors;
R1 = 10 kΩ, R2 = 10 kΩ**

PDTA114E series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–	–50	V
I_o	output current (DC)	–	–100	mA
R1	bias resistor	10	–	kΩ
R2	bias resistor	10	–	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT
	PHILIPS	EIAJ		
PDTA114EE	SOT416	SC-75	03	PDTC114EE
PDTA114EEF	SOT490	SC-89	03	PDTC114EEF
PDTA114EK	SOT346	SC-59	03	PDTC114EK
PDTA114EM	SOT883	SC-101	E5	PDTC114EM
PDTA114ES	SOT54 (TO-92)	SC-43	TA114E	PDTC114ES
PDTA114ET	SOT23	–	*03 ⁽¹⁾	PDTC114ET
PDTA114EU	SOT323	SC-70	*03 ⁽¹⁾	PDTC114EU

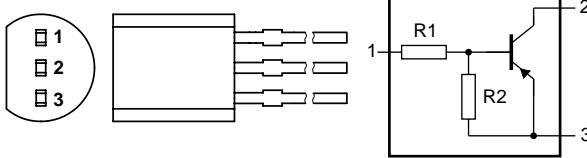
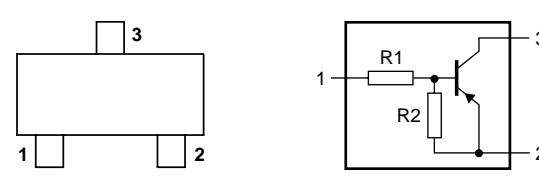
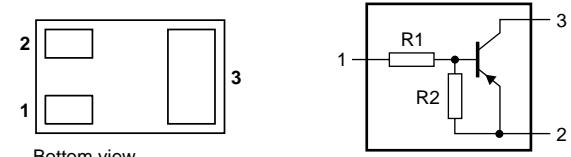
Note

1. * = p: Made in Hong Kong.
- * = t: Made in Malaysia.
- * = W: Made in China.

PNP resistor-equipped transistors;
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PDTA114E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTA114ES	 <p>MAM338</p>	1 2 3	base collector emitter
PDTA114EE PDTA114EEF PDTA114EK PDTA114ET PDTA114EU	 <p>Top view</p> <p>MDB271</p>	1 2 3	base emitter collector
PDTA114EM	 <p>Bottom view</p> <p>MDB267</p>	1 2 3	base emitter collector

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–50	V
V_{CEO}	collector-emitter voltage	open base	–	–50	V
V_{EBO}	emitter-base voltage	open collector	–	–10	V
V_I	input voltage positive negative		– –	+10 –40	V
I_O	output current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–100	mA
P_{tot}	total power dissipation SOT54 SOT23 SOT346 SOT323 SOT416 SOT490 SOT883	$T_{amb} \leq 25^\circ\text{C}$ note 1 note 1 note 1 note 1 note 1 notes 1 and 2 notes 2 and 3	– – – – – – –	500 250 250 200 150 250 250	mW mW mW mW mW mW mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 µm copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient SOT54 SOT23 SOT346 SOT323 SOT416 SOT490 SOT883	in free air note 1 note 1 note 1 note 1 note 1 notes 1 and 2 notes 2 and 3	250 500 500 625 833 500 500	K/W K/W K/W K/W K/W K/W K/W

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 µm copper strip line.

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PDTA114E series

CHARACTERISTICS

$T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{\text{CB}} = -50 \text{ V}$; $I_E = 0$	—	—	-100	nA
I_{CEO}	collector-emitter cut-off current	$V_{\text{CE}} = -30 \text{ V}$; $I_B = 0$	—	—	-1	μA
		$V_{\text{CE}} = -30 \text{ V}$; $I_B = 0$; $T_j = 150 \text{ }^{\circ}\text{C}$	—	—	-50	μA
I_{EBO}	emitter-base cut-off current	$V_{\text{EB}} = -5 \text{ V}$; $I_C = 0$	—	—	-400	μA
h_{FE}	DC current gain	$V_{\text{CE}} = -5 \text{ V}$; $I_C = -5 \text{ mA}$	30	—	—	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}$; $I_B = -0.5 \text{ mA}$	—	—	-150	mV
$V_{i(\text{off})}$	input-off voltage	$I_C = -100 \mu\text{A}$; $V_{\text{CE}} = -5 \text{ V}$	—	-1.1	-0.8	V
$V_{i(\text{on})}$	input-on voltage	$I_C = -10 \text{ mA}$; $V_{\text{CE}} = -0.3 \text{ V}$	-2.5	-1.8	—	V
$R1$	input resistor		7	10	13	$\text{k}\Omega$
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
C_c	collector capacitance	$I_E = i_e = 0$; $V_{\text{CB}} = -10 \text{ V}$; $f = 1 \text{ MHz}$	—	—	3	pF

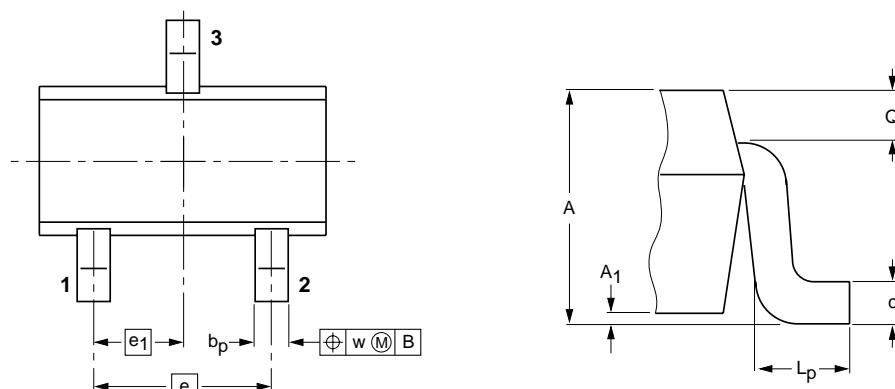
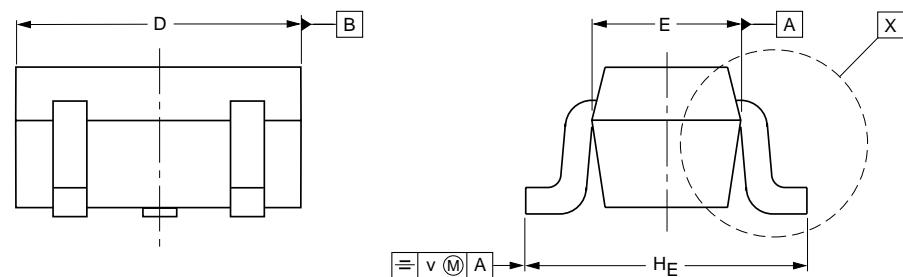
PNP resistor-equipped transistors;
 R1 = 10 k Ω , R2 = 10 k Ω

PDTA114E series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT416



0 0.5 1 mm
 scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

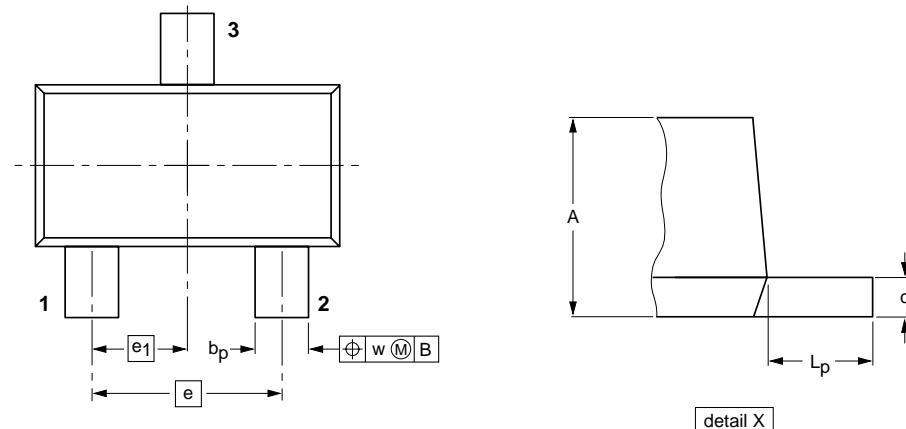
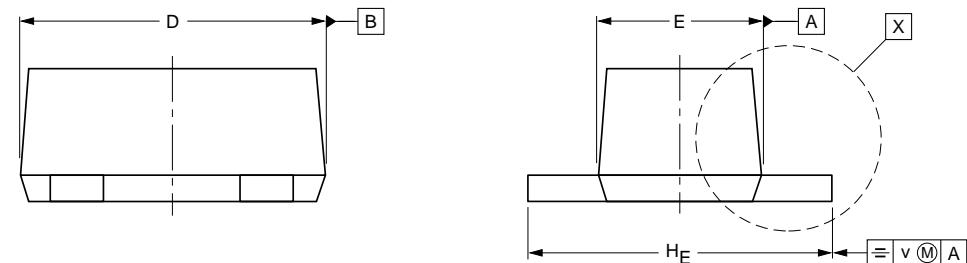
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT416			SC-75			97-02-28

PNP resistor-equipped transistors;
 R1 = 10 k Ω , R2 = 10 k Ω

PDTA114E series

Plastic surface mounted package; 3 leads

SOT490



0 1 2 mm
 scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	H_E	l_p	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

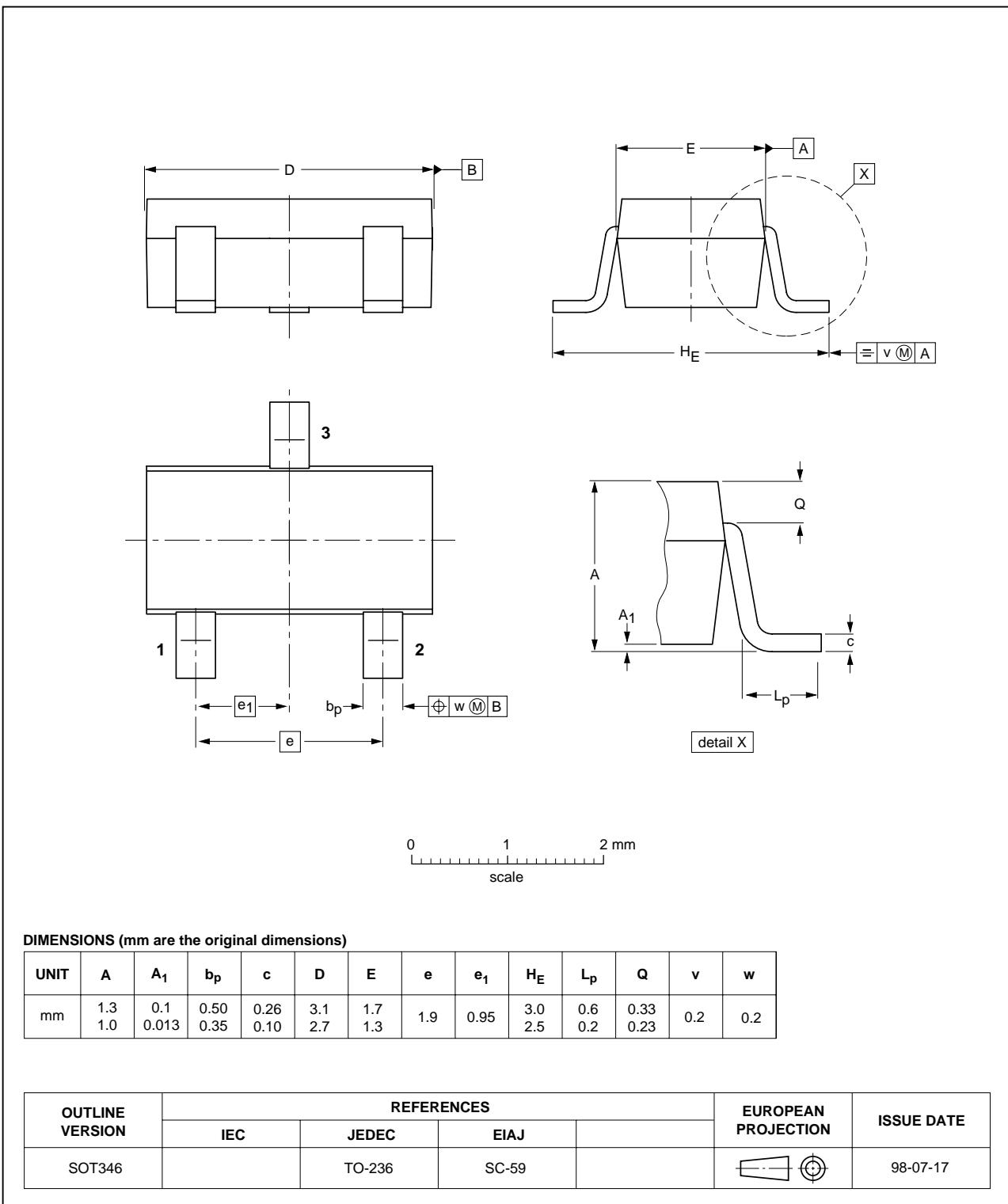
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ	SC-89		
SOT490						98-10-23

PNP resistor-equipped transistors;
 R1 = 10 k Ω , R2 = 10 k Ω

PDTA114E series

Plastic surface mounted package; 3 leads

SOT346

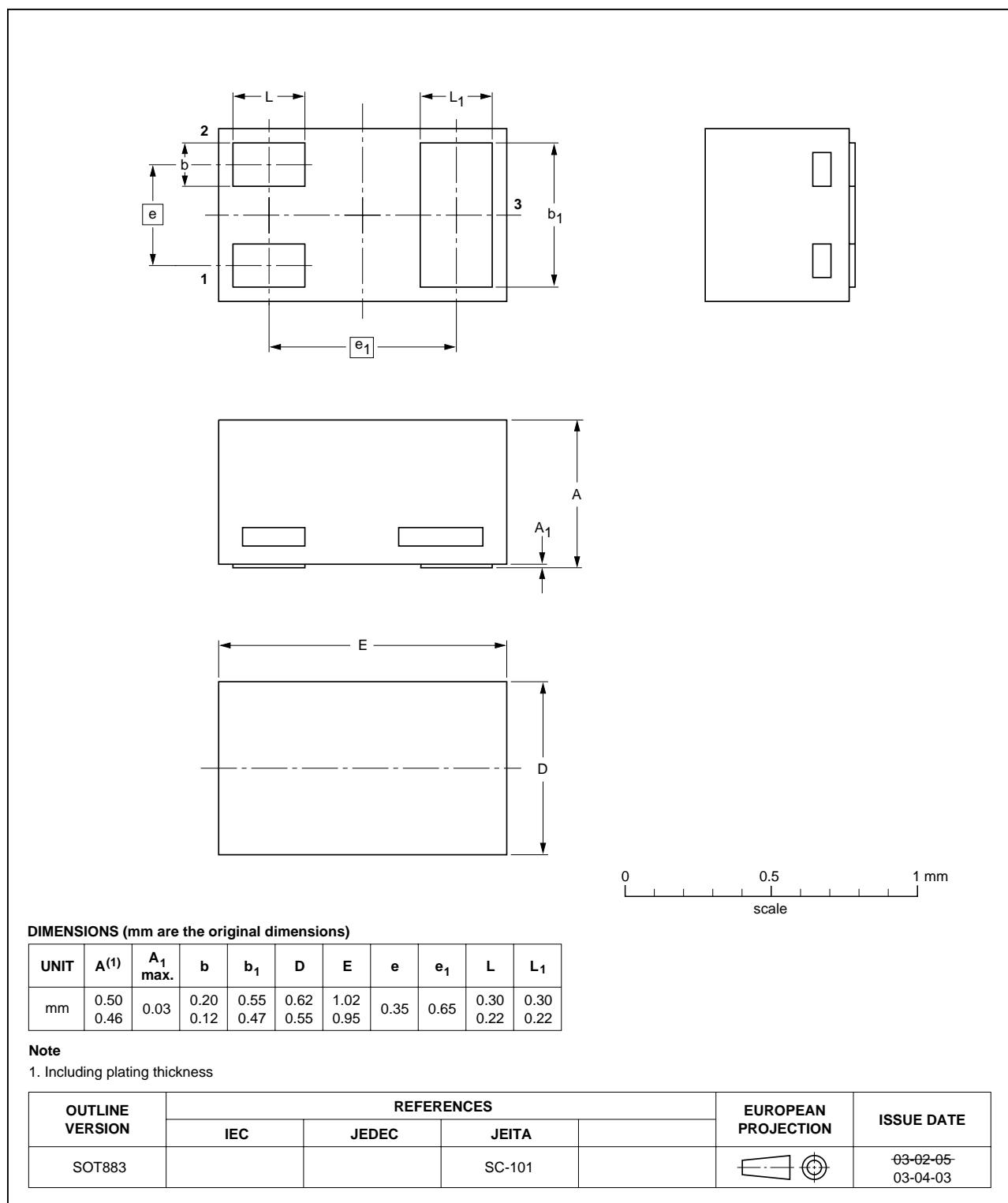


PNP resistor-equipped transistors;
 R1 = 10 k Ω , R2 = 10 k Ω

PDTA114E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

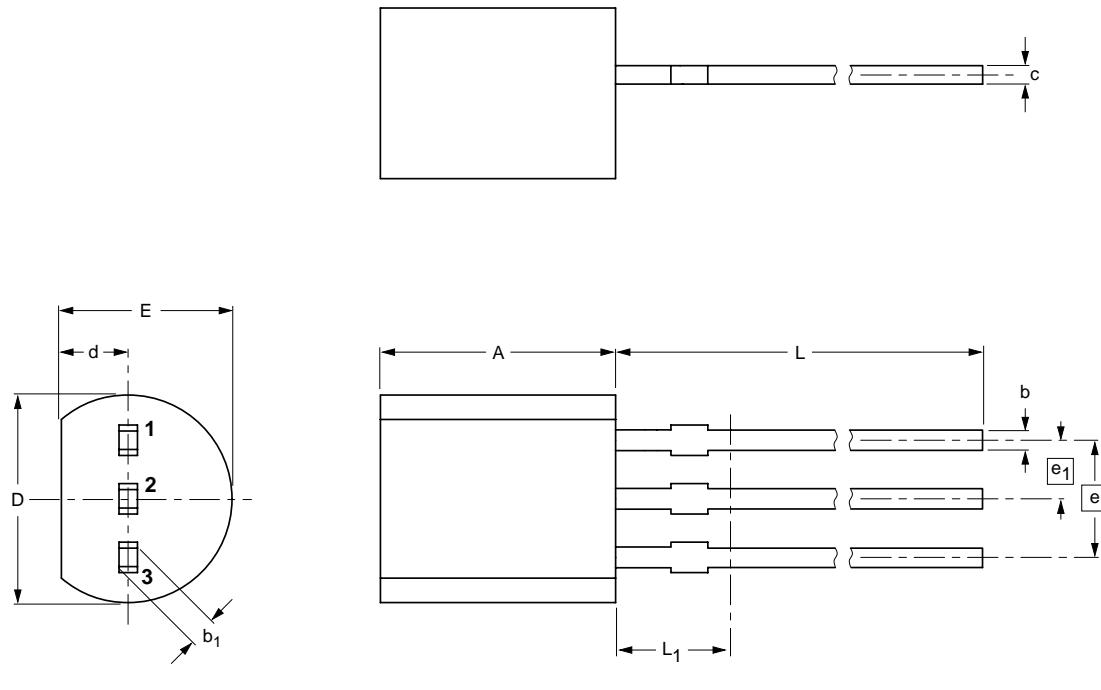


PNP resistor-equipped transistors;
 R1 = 10 kΩ, R2 = 10 kΩ

PDTA114E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



0 2.5 5 mm
 scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

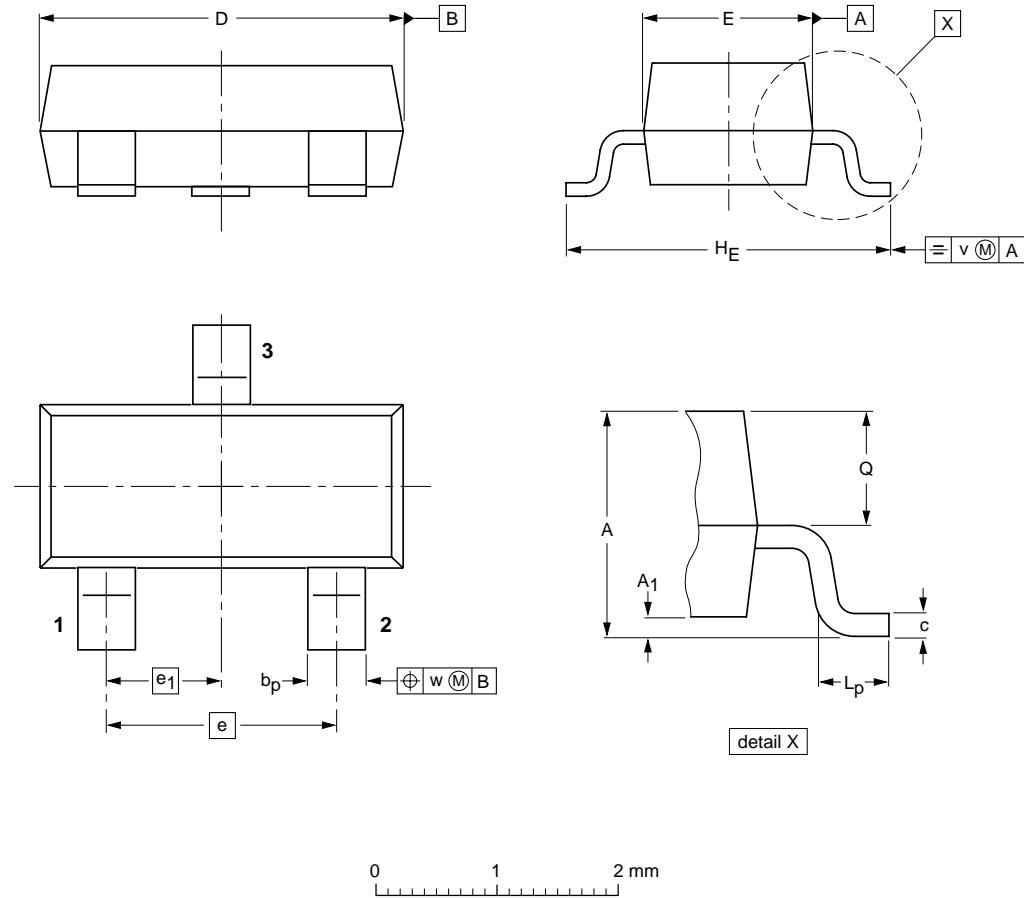
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			-97-02-28 04-06-28

PNP resistor-equipped transistors;
R1 = 10 k Ω , R2 = 10 k Ω

PDTA114E series

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

DIMENSIONS (mm are the original dimensions)													
UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

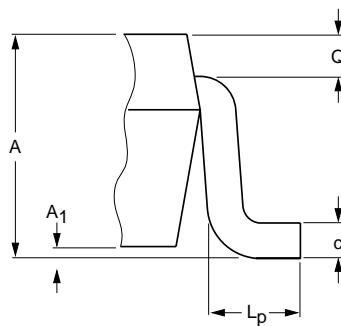
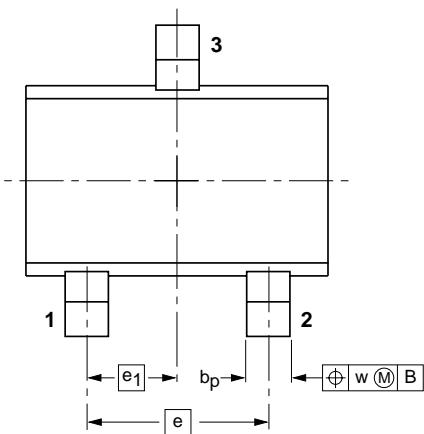
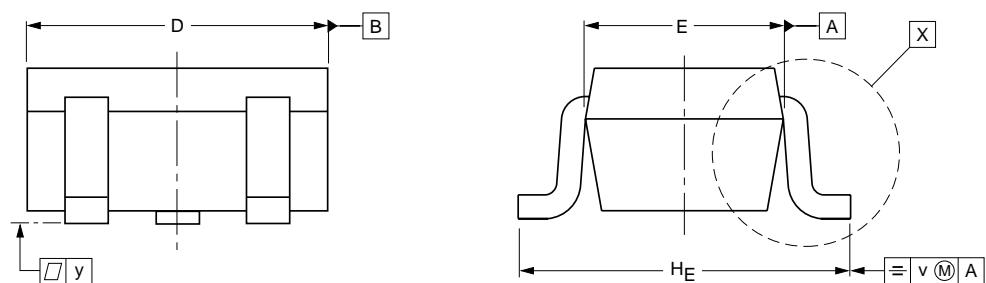
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				-97-02-28 99-09-13

PNP resistor-equipped transistors;
 R1 = 10 k Ω , R2 = 10 k Ω

PDTA114E series

Plastic surface mounted package; 3 leads

SOT323



0 1 2 mm
 scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

PNP resistor-equipped transistors;
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PDTA114E series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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